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RoHS

COMPLIANT

HALOGEN

Thyristor, Surface-Mount, Phase Control SCR, 16 A



D²PAK 2L (TO-263AB 2L)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
I _{T(AV)} 16 A							
V _{DRM} /V _{RRM}	1200 V						
V _{TM}	1.25 V						
I _{GT}	45 mA						
TJ	-40 to +125 °C						
Package	D ² PAK 2L (TO-263AB 2L)						
Circuit configuration	Single SCR						

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC[®]-JESD 47
- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12S2L-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	UNITS								
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu\text{m})$ copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0							

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I _{T(AV)}	Sinusoidal waveform	16	Α					
I _{RMS}		25	A					
V _{RRM} /V _{DRM}		1200	V					
I _{TSM}		350	A					
V _T	16 A, T _J = 25 °C	1.25	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
TJ		-40 to +125	°C					

VOLTAGE RATINGS								
V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} , AT 125 °C mA						
1200	1200	10						
-	REVERSE VOLTAGE V	REVERSE VOLTAGE DIRECT VOLTAGE V V						

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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	тер	TEST CONDITIONS			UNITS		
FARAMETER	STMBOL			TYP.	UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1				
Maximum RMS on-state current	I _{RMS}			2	5	А		
Maximum peak, one-cycle,	I _{TSM}	10 ms sine pulse,	rated V _{RRM} applied	30	00	~		
non-repetitive surge current	ISM	10 ms sine pulse,	no voltage reapplied	3	50			
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4	50	A ² s		
Maximum Peror lusing		10 ms sine pulse,	no voltage reapplied	630		73		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 m	s, no voltage reapplied	6300		A²√s		
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.25		V		
On-state slope resistance	r _t	T.I = 125 °C	T - 125 °C			mΩ		
Threshold voltage	V _{T(TO)}	1j= 123 0		1.0		V		
Maximum reverse and direct leakage current	I _{BM} / I _{DM}	$T_J = 25 \ ^\circ C$	V _R = Rated V _{RRM} /V _{DRM}	0.5				
Maximum reverse and direct leakage current	'RM / 'DM	T _J = 125 °C	VR - Hated VRRM VDRM	1	0			
Holding current	Ι _Η	$ \begin{array}{l} \mbox{VS-25TTS08}, \\ \mbox{VS-25TTS12} \end{array} \begin{array}{l} \mbox{Anode supply} = 6 \ \mbox{V}, \\ \mbox{resistive load, initial } \mbox{I}_T = 1 \ \mbox{A}, \\ \mbox{T}_J = 25 \ \ \mbox{C} \end{array} $		-	150	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$			00			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linea	r to 80 %, $V_{DRM} = R_g - k = open$	n 500		V/µs		
Maximum rate of rise of turned-on current	di/dt				150			

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	vv				
Maximum peak positive gate current	+I _{GM}		1.5	А				
Maximum peak negative gate voltage	-V _{GM}		10	V				
	I _{GT}	Anode supply = 6 V, resistive load, T_J = -10 °C	60	mA				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	45					
		Anode supply = 6 V, resistive load, T_J = 125 °C	20					
		Anode supply = 6 V, resistive load, T_J = -10 °C	2.5					
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	C 2.0					
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V reted value	0.25					
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA				

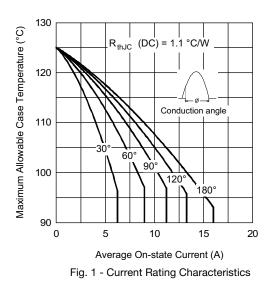
SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs				
Typical turn-off time	tq	1 <u>j</u> = 125 0	110					

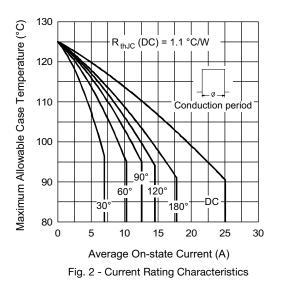


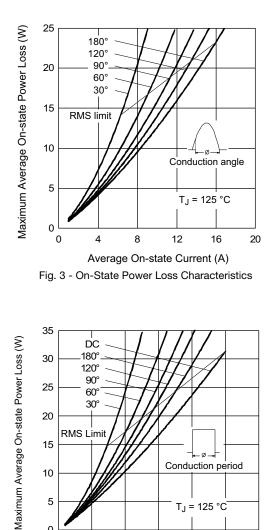
THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Soldering temperature	Τ _S	For 10 s (1.6 mm from case)	260	U					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1						
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	°C/W					
Approximate weight			2	g					
			0.07	oz.					
Marking device		Case style: 2L D ² PAK (2L TO-263AB)	25TT	S12S					

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm] copper 40 °C/W









15

Average On-state Current (A)

10

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3

20

15

10

5

0

0

RMS Limi

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Conduction period

T_J = 125 °C

25

30

20

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VS-25TTS12S2L-M3

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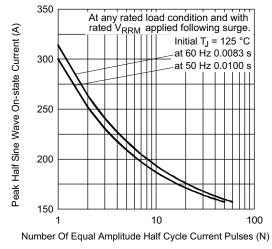
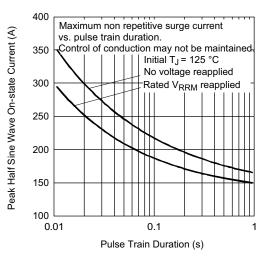
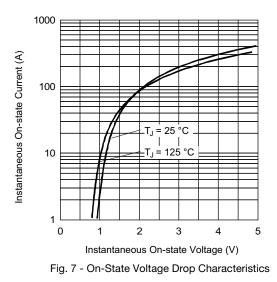
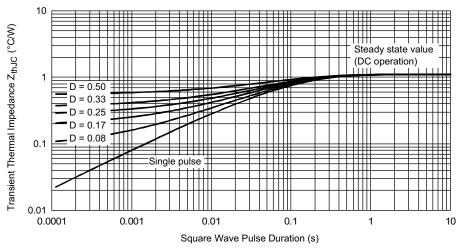


Fig. 5 - Maximum Non-Repetitive Surge Current





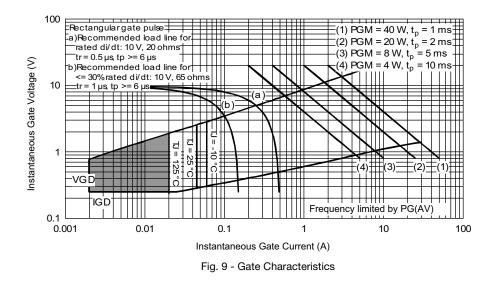




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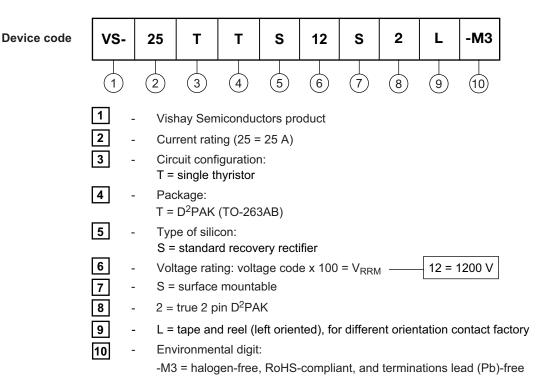
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

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ISHA



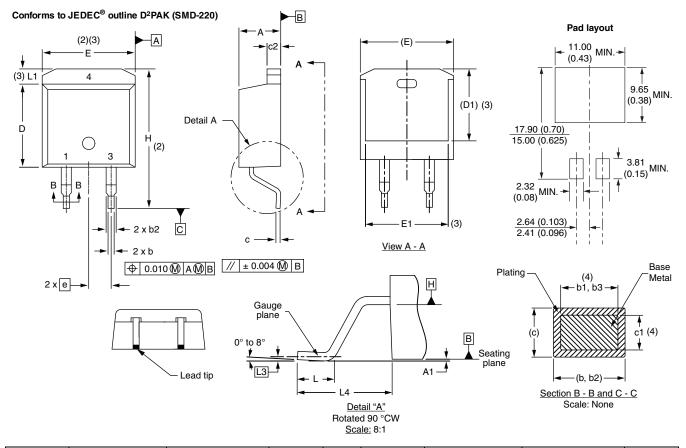
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-25TTS12S2L-M3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96683
Part marking information	www.vishay.com/doc?96693
Packaging information	www.vishay.com/doc?96317



D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES NOTES		INCHES			SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3		
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3		
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3		
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625			
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110			
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3		
c1	0.38	0.58	0.015	0.023	4		L3	0.25	BSC	0.010	BSC			
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208			
D	8.51	9.65	0.335	0.380	2									

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
(3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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